WHAT IS CLAIMED IS:

1. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element; and

irradiating a laser to the fault portions.

2. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element by detecting light emitting positions; and

irradiating a laser to the fault portions.

3. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element; and

irradiating a laser to the fault portions, making the fault portions insulating.

4. A method of manufacturing a light emitting device having a light emitting

element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element by detecting light emitting positions; and

irradiating a laser to the fault portions, making the fault portions insulating.

5. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element; and

irradiating a laser to the fault portions, making inverse direction electric current flow smaller than before the laser irradiation.

6. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element by detecting light emitting positions; and

irradiating a laser to the fault portions, making inverse direction electric current flow smaller than before the laser irradiation.

7. A method of manufacturing a light emitting device according to claim 1, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

8. A method of manufacturing a light emitting device according to claim 2, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

9. A method of manufacturing a light emitting device according to claim 3, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

10. A method of manufacturing a light emitting device according to claim 4, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

11. A method of manufacturing a light emitting device according to claim 5, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

12. A method of manufacturing a light emitting device according to claim 6, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

13. A method of manufacturing a light emitting device according to claim 1, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

14. A method of manufacturing a light emitting device according to claim 2, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

15. A method of manufacturing a light emitting device according to claim 3, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

16. A method of manufacturing a light emitting device according to claim 4, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

17. A method of manufacturing a light emitting device according to claim 5, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

18. A method of manufacturing a light emitting device according to claim 6, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

19. A method of manufacturing a light emitting device according to claim 1, further having at least a thin film transistor.

20. A method of manufacturing a light emitting device according to claim 2, further having at least a thin film transistor.

21. A method of manufacturing a light emitting device according to claim 3, further having at least a thin film transistor.

22. A method of manufacturing a light emitting device according to claim 4, further having at least a thin film transistor.

23. A method of manufacturing a light emitting device according to claim 5, further having at least a thin film transistor.

24. A method of manufacturing a light emitting device according to claim 6, further having at least a thin film transistor.

25. A method of manufacturing a light emitting device according to claim 1, wherein the reverse bias is applied in a range of 1 to 15 V.

26. A method of manufacturing a light emitting device according to claim 2, wherein the reverse bias is applied in a range of 1 to 15 V.

27. A method of manufacturing a light emitting device according to claim 3, wherein the reverse bias is applied in a range of 1 to 15 V.

28. A method of manufacturing a light emitting device according to claim 4, wherein the reverse bias is applied in a range of 1 to 15 V.

29. A method of manufacturing a light emitting device according to claim 5, wherein the reverse bias is applied in a range of 1 to 15 V.

30. A method of manufacturing a light emitting device according to claim 6, wherein the reverse bias is applied in a range of 1 to 15 V.

31. A thin film forming apparatus comprising:

a first film formation chamber for forming an organic compound layer of a light emitting element;

a second film formation chamber for forming an opposing electrode of the light emitting element;

a first processing chamber for applying a reverse bias to the light emitting element, detecting light emission locations of the light emitting element;

a second processing chamber for irradiating a laser to the light emitting element; and

a third processing chamber for sealing a light emitting device.

32. A thin film forming apparatus according to claim 31, wherein the first film

formation chamber is a film formation chamber for performing film formation by an evaporation method, or a film formation chamber for performing film formation by an application method.

33. A thin film forming apparatus according to claim 31, wherein the first processing chamber has: a means for applying a reverse bias within a range of 1 to 15 V to the light emitting element; and a means for detecting the light emission locations.

34. A method of manufacturing a light emitting device using the thin film forming apparatus according to claim 31, comprising the steps of:

detecting the light emission locations in the first processing chamber;

irradiating the laser to the light emission locations in the second processing chamber; and

sealing the light emitting element in the third processing chamber.

35. A method of manufacturing a light emitting device according to claim 1, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.

36. A method of manufacturing a light emitting device according to claim 2, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.

37. A method of manufacturing a light emitting device according to claim 3, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.

38. A method of manufacturing a light emitting device according to claim 4, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.

39. A method of manufacturing a light emitting device according to claim 5, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.

40. A method of manufacturing a light emitting device according to claim 6, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.